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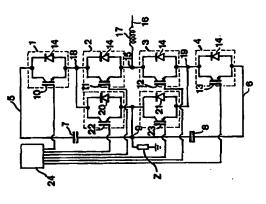
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(54) Title: A CONVERTER DEVICE

(57) Abstract

A univer in conventage gentleming, wonger have under voltage and our conventage gentleming voltage into under voltage and conversately comprises in a series connection between the pole (5, 6, 0 of a direct voltage side at least four units (1-4) each consisting of a semiconductor element ((0-13) of turn-off type and a first unit-point (15) of the series connection is connected to an alternative voltage phase line (16) and forms a phase output. Second interpoints (18, 19) of the series connection are connected to an alternative voltage side (9) through anching to 2 and 21, 23, respectively). An apparatus (2,4) is adapted to control the semiconductor elements (11, 12) with a pulse width modulation frequency of at least one order of magnitude higher than the fundamental frequency of the alternating voltage of the phase line (16) and the rest of the semiconductor elements (10, 13, 22, 23) with a frequency mage one or a couple of times of said fundamental frequency.



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A converter device

FIELD OF THE INVENTION AND PRIOR ART

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nodulation pattern on the phase output of the device by east the mid point, the plus pole and the minus pole of the point and the phase output connected to the mid point of the direct voltage side and an apparatus for controlling the semiconductor elements of the units to generate a train of pulses with determined amplitudes according to a pulse width of a semiconductor element of turn-off type and a first diode ing arranged between two poles, a positive one and a negative one, of a direct voltage side of the device, an alternating voltage phase line connected to a first mid point, which is called phase output, of the series connection between two units while dividing the series connection into two parts, means adapted to provide a mid point between the two poles on said direct voltage side and put these poles on the same voltage but with opposite signs with respect to the mid point of the direct voltage side, a second mid point of each said part of the series connection being through a second diode with the conducting direction with respect to the phase output opposite to the conducting direction of the first diode in the unit arranged between this second mid alternatingly connecting the alternating voltage phase line to at nating voltage into direct voltage and conversely, which comprises a series connection of at least four units each consisting connected in anti-parallel therewith, said series connection be-The present invention relates to a device for converting alterdirect voltage side. ဓ္က 35 25 5 2

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voltage normally is converted into a three-phase alternating voltage or conversely or in so called back-to-back-stations in which atternating voltage is firstly converted into direct voltage and this is then converted into alternating voltage, as well as in SVCs (Static Var Compensator), in which the direct voltage side versely, in which examples of such uses are in stations of HVDC-plants (high voltage direct current), in which direct Such devices may be used in all kinds of situations, in which direct voltage is to be converted into alternating voltage or conconsists of one or more capacitors hanging freely. S 9

may very well find other field of uses. However, the case of backs, when these are used for transmitting high powers, and the present invention aims at a converter device being well suited to transmit high powers, although the invention is not restricted to this field of use, since a converter device of this type transmitting high powers will for this reason hereinafter be discussed for eliminating but not in any way restricting the inven-Such converter devices already known have a number of drawtion. ξ 8

scribed in the IEEE-article IEEE Trans. on Ind. Appln. Vol 32, no converters are described therein, namely multi-level converters with clamping diodes, multi-level converters based upon flying live power, such as for example in HVDC- and back-to-back-applications. The greatest problem of multi-level converters having clamping diodes is that the diode cost will be very high when the number of levels increases, so that for example in the case of converters of this voltage stiff so called VSC-type (Voltage 3, 1996, pages 509-517. Three different types of multi-level capacitors and multi-level converters based upon cascaded converters. Only the two first ones are suitable for transmitting acentials on said phase output. Different types of such multi-level Source Converter) for high power applications have been de-The device defined in the introduction is a so called multi-level converter, since it may deliver at least three different phase po-33 ဓ္က

they require instead a large number of capacitors, and the capacitor size increases with a comparatively large factor when the number of levels is increased, in which this factor is for need of more clamping diodes then said semiconductor elements of turn-off type. The converter devices with flying capacitors require for sure no clamping diodes, but ive levels the number of clamping diodes increases so that example five to six when it is changed from three to five levels. Accordingly, this solution is also very costly.

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SUMMARY OF THE INVENTION

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reduced to a large extend, primarily at an increased number of vice of the type defined in the introduction, which is well suited for high voltage and high power applications and in which the drawbacks mentioned above of such devices already known are The object of the present invention is to provide a converter delevels of the converter.

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second diodes and in the units between the respective second modulation frequency and within or close to the frequency range said alternating voltage phase line and to control the semiconductor elements connected in anti-parallel with said mid point and the respective pole to be turned on and turned off with a frequency being substantially lower than said pulse width This object is according the invention obtained by connecting a of said second diodes in a device of the type mentioned in the introduction, and that the apparatus is adapted to control the semiconductor elements of the units between the two second mid points to be turned on and turned off with a pulse width modulation frequency of at least one order of magnitude higher than the fundamental frequency of the alternating voltage of semiconductor element of turn-off type in anti-parallel with each one or a couple of times said fundamental frequency. 25 8 2

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be of high voltage type, for example hold 4-6 kV instead of 2-3 unit for a series connection of a higher number of said units so Thus, in the present case it will be possible to use a lower number of semiconductor elements connected in series between which means that for this semiconductor elements having a since such high voltage semiconductor elements cannot take Voltages in the order of 10-400 kV are normally handled in devices of this type, and this requires then a series connection of a higher number of semiconductor elements within each said as to distribute the voltage these have to hold in the blocking state among a high number of such semiconductor elements. said second mid point and the respective pole, since these may frequency through which the semiconductor elements first mentioned are switched may for example be 50 or 60 Hz, while the pulse width modulation frequency is typically 1-2 kHz. This means that totally different, more exactly lower, demands are made upon the semiconductor elements first mentioned, which have not to be turned on and turned off with any high frequency, considerable better ability to hold high voltages may be used, high frequencies without unacceptably high switching losses. whereas the semiconductor elements of the "inner" units are turned on and off with a significantly higher frequency, more exactly the so called real pulse width modulation frequency. The way in anti-parallel with said second diodes it is possible to also control the connection of the mid point of the direct voltage side pulse width modulation pattern at the connection of the phase low frequency in the order of the fundamental frequency of the alternating voltage of the alternating voltage phase line, By arranging a semiconductor element of turn-off type in this to the second mid point, and it gets possible to obtain a desired ine to the phase output by turning these semiconductor elements on and off as well as those arranged between said second mid point and the respective pole with a comparatively ဓ္က 23 र 2 S 9

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kV, which means a considerable saving of costs and simplifies

the control of the device. Semiconductor elements with a smaller component area may alternatively be used, which have a higher

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comparatively seldom. The same condition is valid for the switched thermal resistance, but which are available to a low cost, may semiconductor elements connected in anti-parallel with second diodes and switched with a low switching frequency. semiconductor elements these be used for

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advantageously adapted, when said voltage harmonics occur to optionally carry out one or several additional switchings of the second diodes and those in the units between the respective such instabilities, in which the frequency in question may during a very short period of time become for example three times said fundamental frequency, but it is still considerably lower than the semiconductor elements is obtained by this and the advantages mentioned above of the invention with respect to the devices already known will by this be very remarkable. The apparatus is semiconductor elements connected in anti-parallel with said second mid point and the respective pole within a fundamental requency period, in which a switching is defined as comprising a turn-off and turn-on. It may in this way be compensated for nected in anti-parallel with said second diodes and in the units between the respective second mid point and the respective pole with a frequency coinciding with said fundamental frequency in absence of voltage harmonics in the alternating voltage phase line. A large difference in frequency between the control of these semiconductor elements and the other According to a preferred embodiment of the invention the apparatus is adapted to control the semiconductor elements conpulse width modulation frequency. 22 2 ξ 9

els, in which one of them is the mid point of the direct voltage side and just as many are positive as negative, in which said apparatus is adapted to control the semiconductor elements of the units and the semiconductor elements connected in antiparallel with said second diodes to alternatingly connect the alternating voltage phase line to an odd number of different lev-According to another preferred embodiment of the invention the 32 ဓ္က

capacitor (s) are connected in such a way that they across the poles thereof will have a considerably lower voltage than in the case of the flying capacitors of the devices already known, more

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the respective pole as well as the semiconductor elements these inductors and/or filters for extinguishing such harmonics said inductors or transformers, so that stresses thereon may be switching losses may be obtained. Such converter devices with a higher number of levels and the advantages associated therewith may according to this advantageous embodiment of the invention be obtained in a simple way and to a low cost. The advantages of the lower frequency of the semiconductor elements arranged between the respective second mid point and connected in anti-parallel with said second diodes have been discussed above. In addition thereto, this way to arrange a flying capacitor is very advantageous with respect to the arrangement of flying capacitors of the second type mentioned above of converter devices based upon flying capacitors, since a flying example three levels, results in a better adaptation of the pulse width modulation pattern to the sinus wave desired to be obtained downstream of an inductor or transformer arranged in said alternating voltage phase line, so that the harmonics generated during the conversion are reduced or the size of may be reduced, lower voltage differentials may be obtained for reduced and these may be made less costly, and lower hereof to a mid point of said series connection, which is located posite side of the phase output with respect to the connection unit between itself and another capacitor connection or the phase output. Such a multi-level converter device with a higher number of levels than another converter device, which has for mid point, that it comprises (n-3)/2 so called flying capacitors and that each said flying capacitor is connected with one pole between the phase output and the second mid point on the opmid point belonging to the opposite pole thereof and has at least one unit between itself and the second mid point and another number is n, which is at least five, that at least (n-1)/2 of said units are connected in series between the second and the first ဓ္က 5 2 25 S 9

respect to a three-level-converter, and it will be easy to modify a levels of the converter device are nevertheless avoided. A large voltage thereacross is in the invention preferably not more than half the voltage across the entire series connection, which is of a great importance, since the power to be handled by a capacitor is proportional to the square of the voltage, so that the present invention enables a use of flying capacitors while avoiding the large number of clamping diodes which would be mentioned, and the drawbacks of the second type of converter devices based upon flying capacitors has with respect to requirements of very large capacitors for a large number of advantage of a converter device according to this embodiment of the invention is accordingly that it is possible to get a fivelevel-converter to a comparatively low additional cost with necessary in the case of a converter device of the type first exactly the voltage across the flying capacitor with the highest

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across the poles thereof substantially equal to U/4, in which U is said units are adapted to give the flying capacitor a voltage the voltage between the two poles of the direct voltage side. The voltage of the flying capacitor may in this way be kept low and According to a preferred embodiment of the invention n is 5 and the size and the cost thereof may be kept at a low level. 2

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three-level-converter.

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real level of the voltage between the poles of the capacitor, so that the capacitor is upon said connection charged for a voltage level thereof lower than desired and discharged for a voltage level thereof higher than desired. This process is possible apparatus is adapted to control said units, when one pole of said flying capacitors is connected to said phase output so that the phase current passes said capacitor, to make this connection in tential on the phase outlet depending upon the instantaneous thanks to the fact that there are two possible states giving al-According to another preferred embodiment of the invention the one of two ways, which gives substantially the same phase po-35 ဓ

This process means that the capacitance value of the capacitor and the discharging, respectively, which is a suitable factor mally switched in each of the positions for a given switching fremost the same potential on the phase output, in which one state may be used for charging the capacitor and the other for dismay be kept at a minimum, with a time constant for the charging higher than the period of time during which the capacitor is norcharging the capacitor for a given direction of the phase current. quency. S

Further advantages as well as advantageous features of the invention appear from the following description and the other dependent claims.

BRIEF DESCRIPTION OF THE DRAWINGS 5

scription of preferred embodiments of the invention cited as ex-With reference to the appended drawings, below follows a deamples.

In the drawings:

is a circuit diagram illustrating a voltage stiff forced commutated three-level-converter already known connected to an alternating voltage network through induc-Fig 1

tors, in which only one phase leg is shown, 22

ing to a first preferred embodiment of the invention, in which this is connected to a three-phase alternating illustrates a converter device of three-level-type accordvoltage network through inductors, Fig 2 ဓ

illustrates the construction of the device according to Fig 2 for one phase of the alternating voltage network Fig 3

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is a view corresponding to Fig 3 illustrating a five-levelconverter device according to a second preferred embodiment of the invention, and Fig 4

what simplified, of a seven-level-converter device acis a view corresponding to Fig 3 and 4, although somecording to a third preferred embodiment of the invention. S Fig

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DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS OF THE INVENTION 5

ing is only determined by the stray capacitance between the mid grounding of the mid point of the direct voltage side) to a value X (= impedance grounding of the mid point of the direct voltage side, through for example a resistance R or an inductance L) up point of the direct voltage side and ground), so that the potenvice connected to a phase of an alternating voltage phase line is shown in Fig 3, but it is also possible that this constitutes the entire converter device, when this is connected to a one-phase alternating voltage network. The converter device is a so called VSC-converter, which has four units 1-4, usually called transistor valves or alternatively thyristor valves, connected in series Two capacitors 7, 8 connected in series are arranged between said two poles, and a point 9 (the mid point of the direct voltage side) therebetween is connected to ground through an impedance Z, in which this impedance may vary from 0 (= direct o a value Xmax (= ungrounded mid point, in which the ground-Point Clamped)-converter device with clamping diodes of a type well known, and this figure is shown here only for comparing the design of this converter device with a three-level-converter dewhich is shown in Fig 2 and 3 and now will be described with between the two poles 5, 6 of a direct voltage side of the device. vice according to a first preferred embodiment of the invention, reference to these two figures. Only a part of the converter de-The converter device shown in Fig 1 is a so called NPC (Neutral 35 22 8 5 2

respective pole, in which U is the voltage between the two poles

semiconductor elements are required for holding the voltage to The units 1-4 are each made of a semiconductor element 10-13 a so called free-wheeling diode, connected in anti-parallel therewith. Although only one IGBT or GTO per unit has been shown this may stand for a plurality of IGBTs or GTOs connected in series and controlled simultaneously, which also normally is the case, since a comparatively high number of such of turn-off type, such as an IGBT or a GTO, and a first diode 14, be held by each unit in the blocking state. S 9

A first mid point 15 of the series connection between the two verter, is connected to an alternating voltage phase line 16 units 2 and 3, which constitutes the phase output of the conthrough an inductor 17. Said series connection is in this way divided into two equal parts with two units 1, 2 and 3, 4, respeclively, of each such part. ភ

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nected in series so as to distribute the voltage they have to hold in the blocking state among each of them, although one single ducting direction of the first diode in the unit arranged between allel with each second diode. It is also here valid that a great number of semiconductor elements may in practice be connection is through a second diode 20, 21 with a conduction direction with respect to the phase output opposite to the conthis second mid point and the phase output connected to the mid point 9 of the direct voltage side. A semiconductor element 22, 23 of turn-off type, such as an IGBT, is connected in anti-parsemiconductor element has been shown in anti-parallel with A second mid point 18, 19 of each said part of the series con-3 23

the different semiconductor elements and by that ensure that the Furthermore, the device has an apparatus 24 adapted to control 35

ials +U/2 and -U/2, respectively, are in this way provided at the

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side. This apparatus 24 and the arrangement thereof is here very simplified illustrated, and a separate such apparatus could and these receive control signals from a control apparatus arranged on ground level. The function of the apparatus will be as the pole 5, the pole 6 or the mid point 9 of the direct voltage phase output 15 is connected to and receive the same potential in practice be arranged on high potential at each individual unit explained further below.

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The converter device shown in Fig 3 differs with respect to the known shown in Fig 1 by the replacement of the two clamping construction thereof from the NPC-converter device already diodes 20', 21' by a unit consisting of a semiconductor element of turn-off type and a second diode connected in anti-parallel therewith. 5 9

possible to control the semiconductor elements 11, 12 of the units between the two voltage levels desired to be obtained on the phase output 15 are semiconductor element of turn-off type connected in anti-parallel therewith, completely new possibilities to obtain the different By the new characteristic of the invention, i.e. to replace clamping diode by a unit comprising a diode and obtained. More exactly it is 8

respective second mid point have not to be turned on and turned off with a higher frequency than a frequency in the order of said frequency, which preferably is in the order of 1-2 kHz and at least an order of magnitude, usually 20-40 times higher than the fundamental frequency of the alternating voltage of substantially sinusoidal design to be obtained on the alternating voltage phase line 16 on the opposite side of the inductor 17 with respect to the phase output 15. However, through said replacement of the clamping diodes the semiconductor elements 10, 13 of the units located between the respective pole and the second mid points 18, 19 through the apparatus 24 as before to be turned on and turned off with a pulse width modulation 35 22 ဓ

fundamental frequency any longer, in which the frequency in

are also controlled with the same frequency as the and 12 appear clearly from the disclosure above. +U/2 is elements 10 and 11 on, -U/2 is obtained by turning the semiconductor elements 12 and 13 on, while the mid point potential may be obtained either through turning the but this may also be a multiple thereof, such as for example three times the fundamental frequency, especially when voltage which the phase voltage may pass zero at more occasions than two times per period. The semiconductor elements 22 and 23 semiconductor elements 10 and 13. The advantages of not being forced to control the semiconductor elements 10 and 13 obtained on the phase output 15 by turning the semiconductor semiconductor elements 23 and 12 or the semiconductor with the same high frequency as the semiconductor elements 11 question preferably is identical to said fundamental frequency, harmonics occur on the alternating voltage phase line 16, elements 22 and 11 on. 5 S 9

voltage and conversely between a direct voltage side and an It is illustrated in Fig 2 how a converter device according to Fig 3 is designed for converting direct voltage into alternating alternating voltage network with three phases 25, 26, 27. A control for each phase is taking place in accordance with the description made with reference to Fig 3.

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ranged instead of one such unit between each mid point 18 and A converter device with respect to one phase according to a second preferred embodiment of the invention is illustrated in Fig 4 in a view corresponding to Fig 3, and this differs from the units 28-35 between the two poles 5 and 6, in which four are aranged on each side of the phase output 15. Furthermore, two 19 and the respective pole. Moreover, two units 36-39 are arembodiment according to Fig 3 by the series connection of eight units are arranged between the respective second mid point 18, 19, respectively, and the mid point 9 of the direct voltage side. 35 ဓ 25

Finally, a so called flying capacitor 40 is connected with one

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den andra 18, 19 mittpunkten på motsatt sida om fasutgången mot anslutningsmittpunkten tillhörande dess motsatta pol och heter, vilken är belägen mellan nämnda fasutgången 15 och har en enhet mellan sig och den andra mittpunkten och en enhet mellan sig och fasutgången.

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nämligen +U/2, +U/4,0, -U/4 samt -U/2. Hos denna anordning år det meningen att de mellan de andra mittpunkterna 18 och liggande mellan respektive andra mittpunkt och pol samt enheterna 36, 37 och 38, 39 styrs med en betydligt lägre Hos denna anordning är det möjligt att uppnå fem olika 19 liggande enheterna styrs som ovan beskrivits med pulsfrekvens i storleksordningen av den grundfrekvens växelspännivåer på till den första mittpunkten 15 levererade pulser, 34, 29, breddsmoduleringsfrekvens och enheterna 28, ningen på växelspänningsfasledningen 16 har.

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vilka kopplingstillstånd företrädesvis bör användas för att ningsnivåer som kan uppnås på den första mittpunkten 15 och Därvid anger följande kopplingstillståndstabell de spänuppnå dessa spänningsnivåer.

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	28 och 29	30	31	34 och 35	33	32	36 och 37	38 och 39
VaU/2		1	1	٥	٥	0	0	1
V=U/4			۰	0	۰	1	0	1
V=0/4	-	٥	1	0	1	0	0	1
0.0	_	٥	•	٥	1	1	0	1
0 0	°	1	-	_	٥	۰	1	0
Vs-11/4	°	1	٥	-	٥		1	0
V*-U/4	0	0	-	_	-	۰	1	0
0,000		٥	۰		1	-	***	٥

och 0 för Därvid står på konventionellt sätt 1 för tänd släckt. 25

1 and 0 stand in a conventional way for turned on and turned off, respectively.

The following "rules" have been used in this table.

28, 29 and 38, 39, 34, 35 and 36, 37. The following couples have the same state:

28, 29 and 36, 37, 34, 35 and 38, 39 28, 29 and 34, 35 30 and 33 31 and 32 The following couples are complementary:

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36, 37 and 38, 39.

pacitor 40. Which one of these two ways is the one to be used is ing in a charging of the capacitor when the voltage across the to the voltage U/4, in either direction. This may be obtained in determined by the voltage of the flying capacitor 40, so that an apparatus corresponding to the apparatus 24 in Fig 3 controls the different semiconductor elements to choose the way resulttained by switching in the flying capacitor 40, which is charged It appear from the table above that the intermediate voltage levels +U/4 and -U/4, respectively, which voltages may be obtwo different ways, which charges or discharges the flying ca-8 22 5

age thereacross is too high with the aim to keep the voltage across the poles of the capacitor at U/4. The voltage across the capacitor is by that kept almost constant, which means a low poles thereof is too low and a discharging thereof when the voltenergy content and the capacitor may by that be made small, i.e. with a low capacitance. ဓ

We assume for the sake of exemplifying that the frequency of the alternating voltage on the phase line 16 is for example 50 or 60 Hz and the converter only has to deliver active or reactive power at this fundamental frequency. The following is then valid: 35

ation frequency (PWM-frequency) of 1-2 kHz. The inner units

we assume that the converter operates with a pulse width modu-

30-33 will then have a mean switching frequency of half the PWM-frequency, i.e. 0,5-1 kHz. The other units 28, 29, 34, 35,

36, 37 and 38, 39 will only switch with the fundamental fre-

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ferent should that be desired, so that the voltage levels obtained ond mid points and the respective pole may for example be difon the first mid point 15 have another mutual relation than ent mid points of said series connection and between said secrhe distribution of the units arranged on both sides of the differ-

> 37, 38, 39. But also the semiconductor elements 30-33 will have may be chosen, or alternatively semiconductor elements with a 29 and 34, 35) or at 0-voltage (36, 37 and 38, 39). This means that the switching losses will be kept at a low level. This is valid a lower mean switching frequency than the corresponding 3level-converter, so that high voltage semiconductor elements quency (50 or 60 Hz), and they will do so either at 0-current (28, especially for the semiconductor elements 28, 29, 34, 35, 36, smaller area and a higher thermal resistance.

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A seven-level-converter device constructed in the same way as and the function thereof appear from the description of the device according to Fig 4. Thus, two flying capacitors 43 are arranged for obtaining different voltage levels, in which the voltage across the outer capacitor 40 will be U/3 and across the inner capacitor 43 U/6. It is possible to continue in this way and by adding further flying capacitors obtain converter devices with the converter device according to Fig 4 is illustrated in Fig 5, more levels, i.e. 9, 11, ... 5 2

The valves are advantageously so designed that they give the in which $x = 1, \dots \frac{n-3}{2}$ and U is the voltage across the two poles of the direct voltage side. This means for example in the lying capacitors a voltage Ux across the two poles thereof of case of 9 levels $U_1 = U/8$, $U_2 = 2U/8$ and $U_3 = 3U/8$. (n - 1) ⊃ ×

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ferred embodiments described above, but many possibilities to modifications thereof would be apparent to a man with ordinary The invention is of course not in any way restricted to the preskill in the art without departing from the basic idea of the invention.

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shown above.

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CLAIMS

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at least the mid point, the plus pole and the minus pole of the with each of said second diodes, and that the apparatus is adapted to control the semiconductor elements of the units (2, 3, 30-33) between the two second mid points (18, 19) to be turned on and turned off with a pulse width modulation requency of at least one order of magnitude higher than the alternatingly connecting the alternating voltage phase line to element (22, 23) of turn-off type is connected in anti-parallel ohase output connected to the mid point of the direct voltage determined amplitudes according to a pulse width modulation pattern on the phase output (15) of the device by direct voltage side, characterized in that a semiconductor connection being through a second diode (20, 21) with the opposite to the conducting direction of the first diode (14) in the unit arranged between this second mid point and the side and an apparatus (24) for controlling the semiconductor elements of the units to generate a train of pulses with A device for converting alternating voltage into direct voltage and conversely, which comprises a series connection of at conductor element of turn-off type (10-13) and a first diode (14) connected in anti-parallel therewith, said series positive one and a negative one, of a direct voltage side of o a first mid point (15), which is called phase output, of the series connection between two units while dividing the series connection into two parts, means (9) adapted to provide a mid point between the two poles on said direct voltage side and put these poles on the same voltage but with opposite a second mid point (18, 19) of each said part of the series conducting direction with respect to the phase output least four units (1-4, 28-35) each consisting of a semihe device, an alternating voltage phase line (16) connected signs with respect to the mid point of the direct voltage side, connection being arranged between two poles (5,

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semiconductor elements (22, 23) connected in anti-parallel 29, 34, 35) between the respective second mid point and the respective pole to be turned on and turned off with a frequency being substantially lower than said pulse width modulation frequency and within or close to the frequency control the with said second diodes (20, 21) and in the units (1, 4, 28, ange one or a couple of times said fundamental frequency. **£** voltage phase line and alternating

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ments (22, 23) connected in anti-parallel with said second tween the respective second mid point and the respective A device according to claim 1, characterized in that said apparatus (24) is adapted to control the semiconductor elediodes (20, 21) and in the units (1, 4, 28, 29, 34, 35) bepole with a frequency being a multiple of said fundamental requency ۸i

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elements connected in anti-parallel with said second diodes and in the units between the respective second mid point and the respective pole with a frequency coinciding with said fundamental frequency in absence of voltage harmonics in said apparatus (24) is adapted to control the semiconductor A device according to claim 1 or 2, characterized in that he alternating voltage phase line. က

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- of the semiconductor elements connected in anti-parallel with said second diodes and those paratus (24) is adapted to optionally carry out one or several in the units between the respective second mid point and the A device according to claim 3, characterized in that said apadditional switchings 4. ဓ 25
- A device according to any of claims 1-4, characterized in that it has four valves (1-4) with one or more said units connected in series adapted to be controlled simultaneously through the apparatus (24), each of said valves being deů. 35

undamental frequency of the alternating voltage of said

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espective pole within a fundamental frequency period

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espectively are arranged between the phase output (15) and ween the respective mid point (18, 19) and the respective a valve is arranged between the mid point (9) of and that the apparatus (24) is adapted to carry out an alternating connection of three different potential levels to the signed to take substantially the same portion of a voltage applied to one or more such valves connected in series as other such valves when the semiconductor elements included herein are turned off, that two valves (1, 2 and 3, 4), he respective pole (5, 6), that a valve (1,4) is arranged bethe direct voltage side and said second mid point (18, 19), ohase output (15). pole, that

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1)/2 of said units are connected in series between the said flying capacitor is connected with one pole thereof to a mid point (41, 42) of said series connection, which is located between the phase output and the second mid point on the opposite side of the phase output with respect to the connection mid point (41, 42) belonging to the opposite pole thereof and has at least one unit between itself and the with said second diodes to alternatingly connect the roltage side and just as many are positive as negative, in second (18, 19) and the first mid point (15), that it comprises (n-3)/2 so called flying capacitors (40, 43), and that each second mid point and another unit between itself and another to control the semiconductor elements (10-13) of the units and the semiconductor elements (22, 23) connected in anti-parallel evels, in which one of them is the mid point of the direct which said number is n, which is at least five, that at least (n-A device according to any of claims 1-4, characterized in alternating voltage phase line to an odd number of different that the apparatus (24) is adapted sapacitor connection or the phase output. <u>ن</u>

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7. A device according to claim 6, characterized in that n is 5, and that it has one said flying capacitor (40). 33

units are adapted to give the flying capacitor (40) a voltage across the poles thereof substantially equal to U/4, in which U is the voltage between the two poles of the direct voltage A device according to claim 7, characterized in that said ω.

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tive direct voltage pole, that two valves (28, 29, 34, 35) are arranged between the respective second mid point and the respective direct voltage pole, that a valve (31, 32) is arranged between the respective connection (41, 42) of the flying capacitor (40) to the series connection and the phase ies between the mid point of the direct voltage side and said each valve is adapted to take substantially the same portion of a voltage applied to one or more such valves connected in 35) are arranged between the phase output and the respecoutput (15), and that two valves (36-39) are connected in sesaid series connection has eight valves (28-35), in which series as other such valves when the semiconductor elements included therein are turned off, that four valves (28-A device according to claim 7 or 8, characterized in that 6

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10. A device according to claim 6, characterized in that n is 7.

second mid point.

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11.A device according to claim 9, characterized in that it has two flying capacitors (40, 43), and that the inner capacitor (43) connected by the poles thereof to said series connection closest to the phase output (15) is adapted to have a voltage of U/6 across the poles thereof and the second, outer capacitor (40) is adapted to have a voltage of U/3 across the soles thereof, in which U is the voltage between the two 22 8

poles of the direct voltage side.

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12.A device according to claim 6, characterized in that the valves are adapted to give the flying capacitors (40, 43) a voltage U_x across the two poles thereof of $\frac{x \cdot U}{(n-1)}$, in which $x = 1, \dots \frac{n-3}{2}$ and U is the voltage across the two poles of the

direct voltage side.

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gives substantially the same phase potential on the phase outlet depending upon the instantaneous real level of the voltage between the poles of the capacitor, so that the ca-13.A device according to any of claims 6-12, characterized in that the apparatus (24) is adapted to control said unit, when one pole of said flying capacitors (40, 43) is connected to said phase output so that the phase current passes said capacitor, to make this connection in one of two ways, which pacitor is upon said connection charged for a voltage level hereof lower than desired and discharged for a voltage level hereof higher than desired.

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14.A device according to any of claims 1-13, characterized in that said semiconductor elements are IGBTs (Insulated Gate Bipolar Transistor).

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15.A device according to any of claims 1-13, characterized in that said semiconductor elements are GTOs (Gate Turn-Off thyristor).

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16.A device according to any of claims 1-15, characterized in that said direct voltage side is formed by a direct voltage network for transmitting high voltage direct current (HVDC) and the alternating voltage phase line belongs to an alternating voltage network.

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17.A device according to any of claims 1-15, characterized in that it is a part of a SVC (Static Var Compensator) with the direct voltage side formed by capacitors hanging freely and

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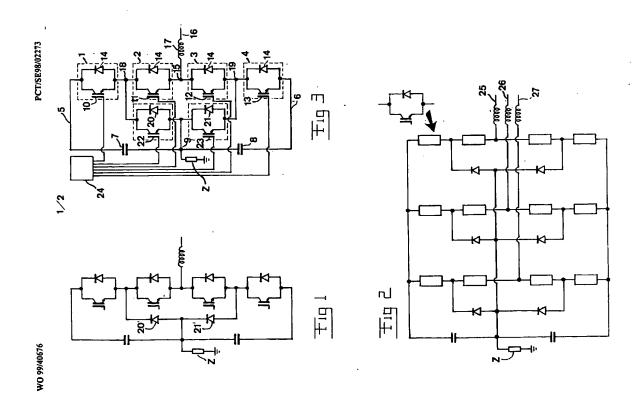
the alternating voltage phase line belonging to an alternating voltage network. 18. A device according to any of claims 1-17, characterized in

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work, and that it comprises one said series connection and 25-27) included in a multiple-phase alternating voltage netsecond diodes associated therewith and semiconductor elements of turn-off type connected in anti-parallel therewith for each phase line connected in parallel with each other that it has at least two alternating voltage phase lines (16, between said poles of the direct voltage side.

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19.A device according to claim 18, characterized in that the number of phases of the alternating voltage network is three.



INTERNATIONAL SEARCH REPORT

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-1" document which may throw doubts on priority claims) or which is "A" document defining the general state of the art which is not considered to be of particular relovance C. DOCUMENTS CONSIDERED TO BE RELEVANT document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another clusion or other special reason (as specified) Date of the actual completion of the international search document referring to an oral disclosure, use, exhibition or other A. CLASSIFICATION OF SUBJECT MATTER SE, DK, FI, NO classes as above Name and mailing address of the ISA/ Swedish Patent Office Box 5055, S-102 42 STOCKHOLM IPC6: H02M, H03J, H03K B. FIELDS SEARCHED 18 February 1999 WPI, PAJ ò

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